

**Amendments to the Claims**

This listing of claims will replace all prior version, and listings, of claims in the application:

**Listing of Claims:**

1-57. (Canceled)

58. (Currently amended) The light emitting device ~~laser~~-recited in claim 5760, wherein said first oxidizable layer further comprises a second region which is not significantly oxidized.

59. (Canceled)

60. (Currently Amended) A light emitting device comprising:

a first mirror;

a light emitting active layer disposed above said first mirror;

at least a first oxidizable layer having an oxidized region which is significantly oxidized, said first oxidizable layer being disposed above said light emitting active layer;

at least one semiconductor layer residing above at least a portion of said first oxidizable layer;

a second mirror disposed above said light emitting active layer;

top and bottom electrical contacts disposed to communicate with said light emitting active layer;

interconnect metallization deposited above at least a portion of said semiconductor layer and in contact with said top electrical contact; and

at least one basin disposed proximal to said oxidized region~~The laser recited in claim 59~~, wherein said basin is provided for allowing said first region to be oxidized.

61. (Currently amended) The light emitting device ~~laser~~-recited in claim 5760, wherein said top electrical contact is characterized by a center.

62. (Currently amended) The light emitting device~~laser~~ recited in claim 61, ~~further comprising at least one pit disposed proximal to said oxidized region, wherein said pit basin does not hemming-hem~~ said center.

63. (Currently amended) A light emitting device comprising:

a first mirror;

a light emitting active layer disposed above said first mirror;

at least a first oxidizable layer having an oxidized region which is significantly oxidized, said first oxidizable layer being disposed above said light emitting active layer;

at least one semiconductor layer residing above at least a portion of said first oxidizable layer;

a second mirror disposed above said light emitting active layer;

top and bottom electrical contacts disposed to communicate with said light emitting active layer, said top electrical contact being characterized by a center;

interconnect metallization deposited above at least a portion of said semiconductor layer and in contact with said top electrical contact; and

at least one pit disposed proximal to said oxidized region, said pit not hemming said center~~The laser recited in claim 62~~, wherein said pit is provided for allowing said first region to be oxidized.

64. (Currently amended) The light emitting device ~~laser~~ recited in claim ~~57~~60, wherein said semiconductor layer has an electrically insulating region formed by ion implantation.

65. (Currently amended) The light emitting device~~laser~~ recited in claim 64, wherein said electrically insulating region resides above at least a portion of said oxidized region.

66. (New) The light emitting device recited in claim 63, wherein said semiconductor layer has an electrically insulating region formed by ion implantation.

67. (New) The light emitting device recited in claim 66, wherein said electrically insulating region resides above at least a portion of said oxidized region.

68. (New) A light emitting device comprising:

- a first mirror;
- a light emitting active layer disposed above said first mirror;
- at least a first oxidizable layer having an oxidized region which is significantly oxidized, said first oxidizable layer being disposed above said light emitting active layer;
- at least one semiconductor layer residing above at least a portion of said first oxidizable layer;
- a second mirror disposed above said light emitting active layer;
- top and bottom electrical contacts disposed to communicate with said light emitting active layer;
- interconnect metallization deposited above at least a portion of said semiconductor layer and in contact with said top electrical contact; and
- at least one pit disposed proximal to said oxidized region, said pit not hemming said top electrical contact, wherein said pit is provided for allowing said first region to be oxidized.

69. (New) The light emitting device recited in claim 68, wherein said semiconductor layer has an electrically insulating region formed by ion implantation.

70. (New) The light emitting device recited in claim 69, wherein said electrically insulating region resides above at least a portion of said oxidized region.